

# Si Zener-diode Chip — TK2210FZD

## 1. Scope

- The specification applies to flip Zener diode.
- Extra lower leakage current
- Special thickness for special assembly process.

## 2. Structure

- Planar type Zener diode.
- Front side Metal : Au-Sn (Ag/Sn for option)
- Back side Metal : Si

## 3. Size

- Chip Size : 21.0mil×9.0mil±0.8mil (0.540mm×0.240mm ± 0.020mm)
- Thickness : 4.3mil/5.0mil±0.6mil (0.110mm/0.150mm ± 0.015mm)
- Pad Size : 8.0mil×8.0 mil±0.4mil (0.200mm ×0.200mm ± 0.010mm)
- Pad Gap : 4.5mil ±0.8mil (100um±0.020mm)
- Pattern drawing : per fig 1.

## 4. Electrical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V <sub>F</sub>	Rank C: I <sub>z</sub> = 10 mA	7		9	V
		Rank F: I <sub>z</sub> = 10 mA	13		16	V
		Rank G: I <sub>z</sub> = 10 mA	16		24	V
		Rank L: I <sub>z</sub> = 10 mA	38		48	V
		Rank M: I <sub>z</sub> = 10 mA	47		57	V
Forward Leakage current	I <sub>F</sub>	Rank C, F, G: V <sub>F</sub> = 5 V			500	nA
		Rank L: V <sub>F</sub> = 30V			1000	nA
		Rank M: V <sub>F</sub> = 40V				
Reverse Zener Voltage	V <sub>Z</sub>	Rank C: I <sub>z</sub> = 10 mA	7		9	V
		Rank F: I <sub>z</sub> = 10 mA	13		16	V
		Rank G: I <sub>z</sub> = 10 mA	16		24	V
		Rank L: I <sub>z</sub> = 10 mA	38		48	V
		Rank M: I <sub>z</sub> = 10 mA	47		57	V
pReverse Leakage current	I <sub>R</sub>	Rank C, F, G: V <sub>R</sub> = 5 V			500	nA
		Rank L: V <sub>F</sub> = 30V			1000	nA
		Rank M: V <sub>F</sub> = 40V				

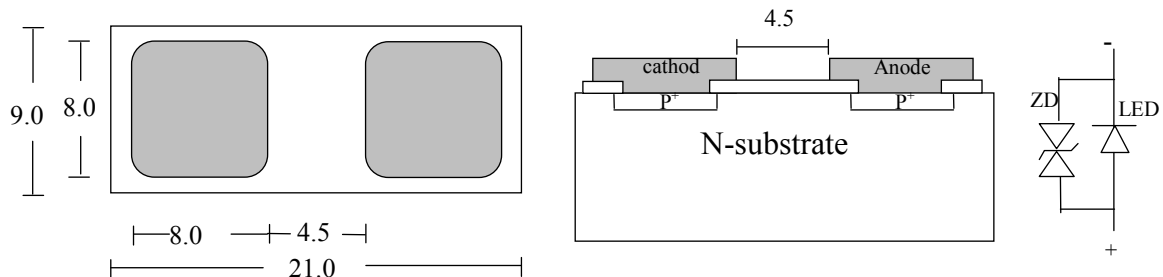


fig. 1  
Unit : mil

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